

SILICON DIOXIDE DEPOSITION METHOD AND APPARATUS

Abstract

In plasma enhanced chemical vapor deposition (PECVD) of silicon
dioxide on a substrate, voids and discontinuities are reduced by first depositing
silicon dioxide in a sputter etch chamber (22) in which a magnetic field is produced
within the rf plasma for depositing the silicon dioxide. Simultaneous sputter etch
and deposition occurs which inhibits net deposition at the corners of metal
conductors over which the silicon dioxide is deposited. The substrate is then
removed and transferred through a load lock (27) to a conventional PECVD
deposition chamber (23).

This Sheet Has Been Replaced

